GTM CORPORATION

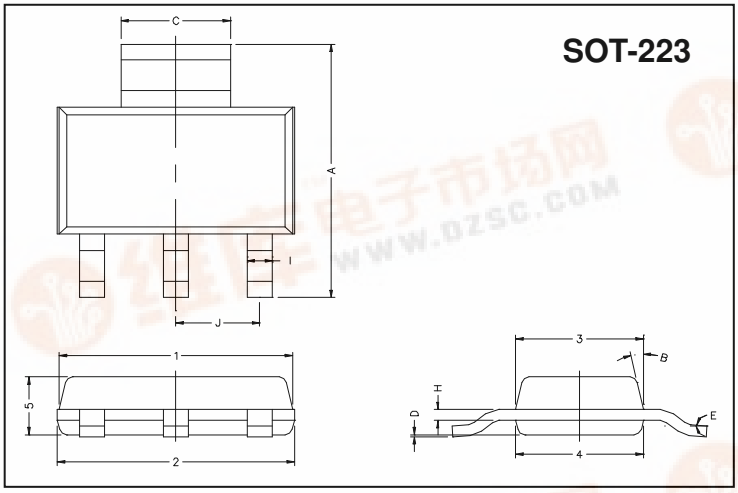
ISSUED DATE :2002/10/28
REVISED DATE :2006/05/10C

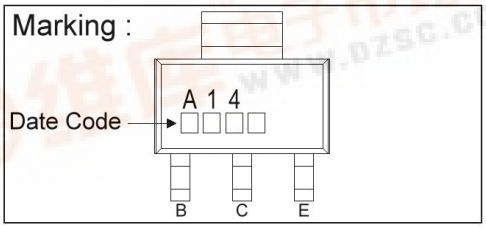
GLA14 NPN EPITAXIAL PLANAR TRANSISTOR

Description

The GLA14 is a Darlington amplifier transistor designed for applications requiring extremely high current gain.

Package Dimensions





REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	6.70	7.30	B	13°TYP.	
C	2.90	3.10	J	2.30 REF.	
D	0.02	0.10	1	6.30	6.70
E	0°	10°	2	6.30	6.70
I	0.60	0.80	3	3.30	3.70
H	0.25	0.35	4	3.30	3.70
			5	1.40	1.80

Absolute Maximum Ratings at Ta = 25℃

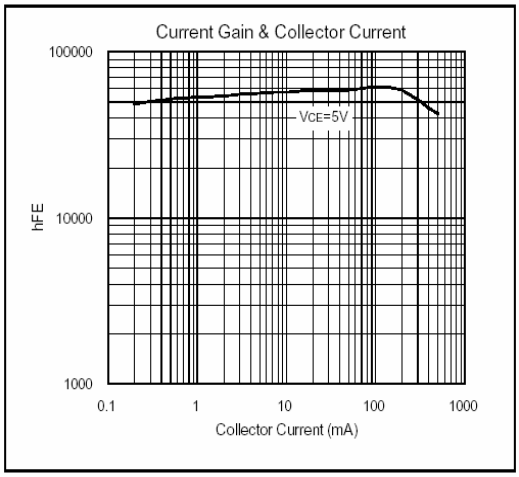
Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	℃
Storage Temperature	Tstg	-55~+150	℃
Collector to Base Voltage	V_{CBO}	30	V
Collector to Emitter Voltage	V_{CEO}	30	V
Emitter to Base Voltage	V_{EBO}	10	V
Collector Current	I_C	500	mA
Total Power Dissipation	P_D	2	W

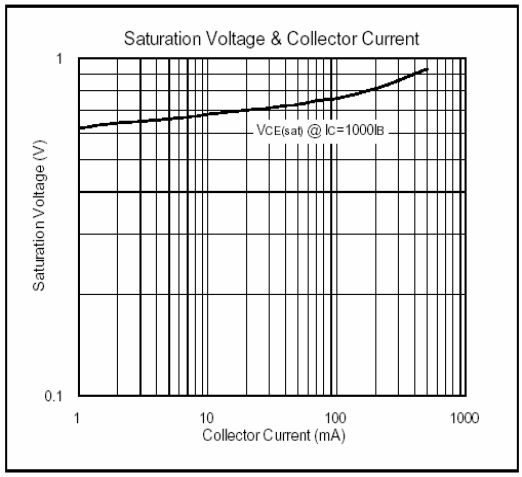
Electrical Characteristics (Ta = 25℃ unless otherwise noted)

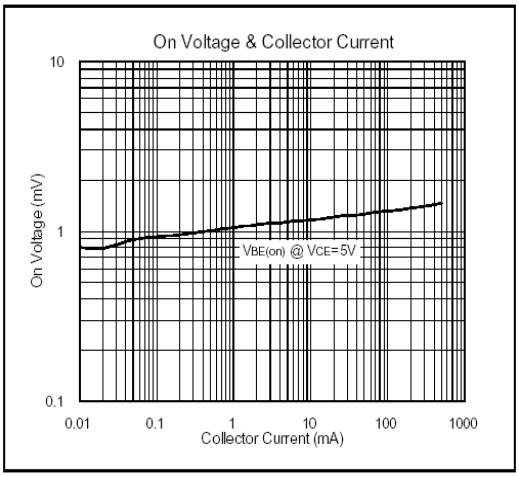
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV_{CBO}	30	-	-	V	I_C=100uA, I_E=0
BV_{CEO}	30	-	-	V	I_C=100uA, I_B=0
BV_{EBO}	10	-	-	V	I_E=10uA, I_C=0
I_{CBO}	-	-	100	nA	V_{CB}=30V, I_E=0
I_{EBO}	-	-	100	nA	V_{EB}=10V, I_C=0
*$V_{CE(sat)}$	-	-	1.5	V	I_C=100mA, I_B=0.1mA
*$V_{BE(on)}$	-	-	2.0	V	V_{CE}=5V, I_C=100mA
*h_{FE1}	10K	-	-		V_{CE}=5V, I_C=10mA
*h_{FE2}	20K	-	-		V_{CE}=5V, I_C=100mA
fT	125	-	-	MHz	V_{CE}=5V, I_C=10mA, f=100MHz
Cob	-	-	6	pF	V_{CB}=10V, I_E=0, f=1MHz

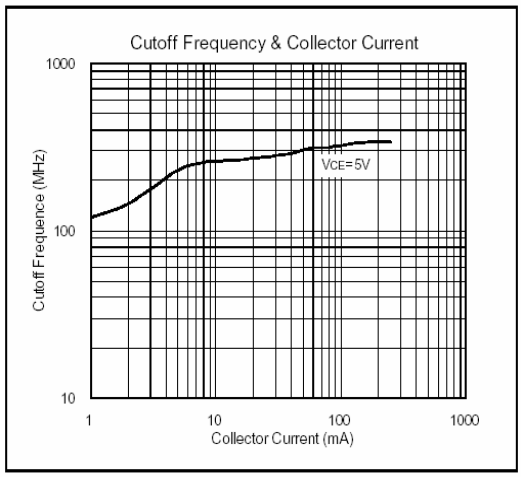
*** Pulse Test: Pulse Width≦380μs, Duty Cycle≦2%**

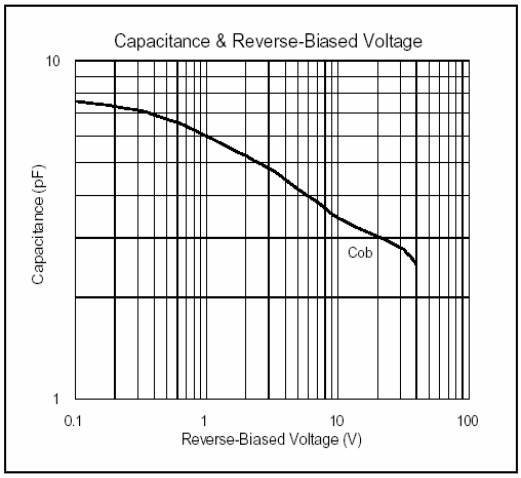
Characteristics Curve

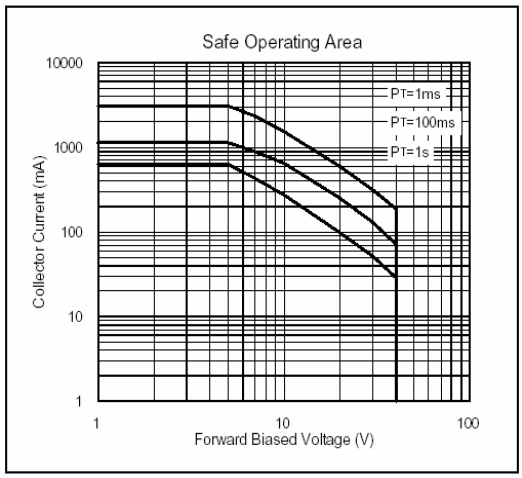












Head Office And Factory:
- **Taiwan**: No. 17-1 Tatung Rd. Fu Kou Hsin-Chu Industrial Park, Hsin-Chu, Taiwan, R. O. C.
  TEL : 886-3-597-7061 FAX : 886-3-597-9220, 597-0785
- **China**: (201203) No.255, Jang-Jiang Tsai-Lueng RD. , Pu-Dung-Hsin District, Shang-Hai City, China
  TEL : 86-21-5895-7671 ~ 4 FAX : 86-21-38950165